Electronic Supplementary Information (ESI) for

Antiferromagnetic Topological Insulator MnBi₂Te₄: Synthesis and

Magnetic properties Electronic

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Figure S1. Experimental and reference PXRD patterns of (a) MnTe, (b) Bi_2Te_3 and (c) Product 1. (d) Product 2



Figure S2. HAADF-STEM image for the (0 1 0) crystallographic plane of Product 2. Inset: enlarged HAADF-STEM image superimposed with the schematic structure of the (0 1 0) crystallographic plane of $MnBi_2Te_4$ and Bi_2Te_3 .



Figure S3. Survey XPS spectra of (a) fresh and (b) oxidized MnBi₂Te₄ surfaces.



Figure S4. (a) EDX spectrum of oxidized MnBi₂Te₄. (b) Raman spectrum of oxidized and fresh MnBi₂Te₄.



Figure S5. Suppression of T_N with increasing applied magnetic fields.